

DOCKET NO: 241280US2S DIV

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF :
TSUTOMU SATO ET AL. :
SERIAL NO: NEW APPLICATION :ATT: APPLICATION DIVISION
FILED: HEREWITH :
FOR: SEMICONDUCTOR DEVICE :
FORMED IN SEMICONDUCTOR LAYER
ARRANGED ON SUBSTRATE WITH
ONE OF INSULATING FILM AND
CAVITY INTERPOSED BETWEEN THE
SUBSTRATE AND THE
SEMICONDUCTOR LAYER

PRELIMINARY AMENDMENT

COMMISSIONER FOR PATENTS
ALEXANDRIA, VIRGINIA 22313

SIR:

Prior to examination on the merits, please amend the above-identified application as follows:

Amendments to the Specification begin on page 2 of this paper.

Amendments to the Claims are reflected in the listing of claims which begins on page 3 of this paper.

Remarks begin on page 6 of this paper.